

TSM60N03 30V N-Channel Power MOSFET

SEMICONDUCTOR



TO-252 (DPAK)



Pin Definition:

- 1. Gate
- 2. Drain
- 3. Source

PRODUCT SUMMARY

V _{DS} (V)	$R_{DS(on)}(m\Omega)$	I _D (A)
30	4.5 @ V _{GS} =10V	60

Features

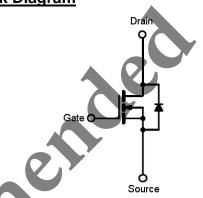
- Advanced Trench Technology
- Low $R_{DS(ON)} 4.5 m\Omega$ (Max.)
- Low gate charge typical @ 12nC (Typ.)
- Low Crss typical @ 140pF (Typ.)

Ordering Information

Part No.	Package	Packing
TSM60N03CP ROG	TO-252	2.5Kpcs / 13" Reel

Note: "G" denote for Halogen Free Product





N-Channel MOSFET

Absolute Maximum Rating (T_C = 25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V_{DS}	30	V	
Gate-Source Voltage		V_{GS}	±20	V	
	T _c = 25°C	I _D	60		
Continuous Drain Current	$T_C = 70^{\circ}C$		48	А	
Continuous Diain Current	$T_A = 25^{\circ}C$		19		
	$T_A = 70^{\circ}C$		15		
Drain Current-Pulsed *		I _{DM}	140	Α	
Avalanche Current, L = 0.1mH		I_{AS}, I_{AR}	38	Α	
Avalanche Energy, L = 0.1mH		E_{AS},E_{AR}	72	mJ	
	$T_C = 25^{\circ}C$		41	W	
Maximum Pawer Distinction	$T_C = 70^{\circ}C$	D	26		
Maximum Power Dissipation	$T_A = 25^{\circ}C$	P_D	2.5		
	$T_A = 70^{\circ}C$		1.6		
Storage Temperature Range		T_{STG}	-55 to +150	°C	
Operating Junction Temperature Range		TJ	-55 to +150	°C	

^{*} Limited by maximum junction temperature

Thermal Performance

Parameter	Symbol	Limit	Unit
Thermal Resistance - Junction to Case	R _{eJC}	3	°C/W
Thermal Resistance - Junction to Ambient	$R_{\Theta JA}$	50	°C/W

Notes: Surface mounted on FR4 board t ≤ 10sec

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Electrical Specifications (T_C = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250uA$	BV _{DSS}	30			V
Drain Source On State Registeres	$V_{GS} = 10V, I_D = 19A$	R _{DS(ON)}		3.5	4.5	mΩ
Drain-Source On-State Resistance	$V_{GS} = 4.5V, I_D = 16A$	R _{DS(ON)}		4.6	5.8	mΩ
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250uA$	$V_{GS(TH)}$	1.15		2.2	V
Zero Gate Voltage Drain Current	$V_{DS} = 30V, V_{GS} = 0V$	I _{DSS}			1	uA
Gate Body Leakage	$V_{GS} = \pm 20V, V_{DS} = 0V$	I _{GSS}			±100	nA
Dynamic						
Total Gate Charge	\/ 4E\/ 40A	Q_g		12		
Gate-Source Charge	$V_{DS} = 15V, I_{D} = 19A,$ $V_{GS} = 4.5V$	Q_gs		5.4		nC
Gate-Drain Charge		Q_{gd}		4.6		
Input Capacitance	\/ 45\/ \/ 0\/	C _{iss}		1700		
Output Capacitance	$V_{DS} = 15V, V_{GS} = 0V,$ f = 1.0MHz	Coss	7	350		pF
Reverse Transfer Capacitance	1 = 1.0IVII IZ	C _{rss}		140		
Switching						
Turn-On Delay Time		$t_{d(on)}$		25		
Turn-On Rise Time	$V_{GS} = 4.5V, V_{DS} = 15V,$	t _r		20		nS
Turn-Off Delay Time	$R_G = 1.5\Omega, I_D = 10A$	$t_{d(off)}$		25		113
Turn-Off Fall Time		t _f		15		
Drain-Source Diode Characteristics and Maximum Rating						
Drain-Source Diode Forward Voltage	$V_{GS} = 0V, I_{S} = 10A$	V _{SD}	-	0.8	1.2	V
Reverse Recovery Time	$I_S = 10A$, $T_J = 25$ °C	t _{fr}		25		nS
Reverse Recovery Charge	dl/dt = 100A/us	Q_{fr}		17		nC

Notes:

- Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
 R_{θJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design. $R_{\theta JA}$ shown below for single device operation on FR-4 in still air

The maximum current rating is limited by package



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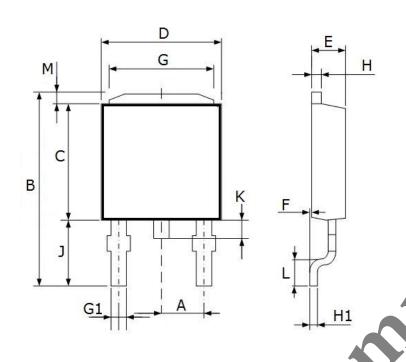


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TO-252 Mechanical Drawing



TO-252 DIMENSION						
DIM	MILLIM	ETERS	INCHES			
ווועו	MIN	MAX	MIN	MAX		
Α	2.286 BSC 0.090		BSC			
В	9.40	10.40	0.370	0.409		
С	5.40	6.23	0.213	0.245		
D	6.40	6.80	0.252	0.268		
Е	2.20	2.40	0.087	0.094		
F	0.00	0.20	0.000	0.008		
G	5.20	5.50	0.205	0.217		
G1	0.50	0.91	0.020	0.036		
Н	0.45	0.60	0.018	0.024		
H1	0.40	0.60	0.016	0.024		
	2.50	2.90	0.098	0.114		
K	0.60	1.00	0.023	0.039		
7	1.40	1.78	0.055	0.070		
М	0.88	1.28	0.034	0.050		

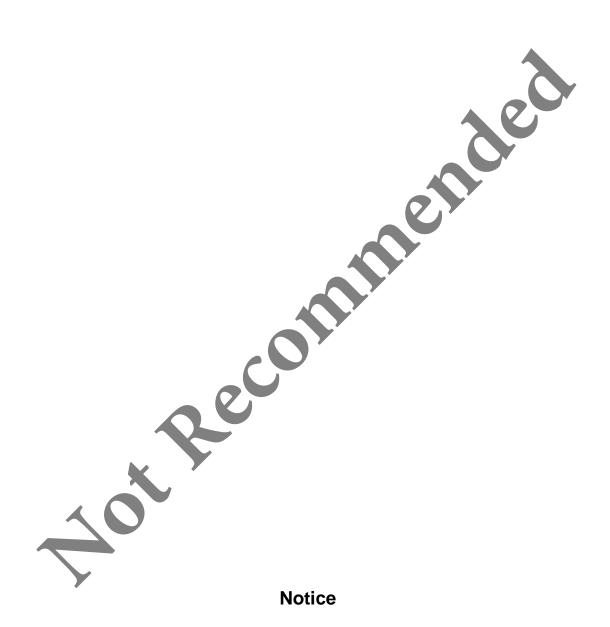
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